

a second electrode formed on the dielectric as a layer of [only] tungsten nitride, the layer of tungsten nitride including silicon.

49. (Amended) The capacitor of claim 46, wherein the layer of [only] tungsten nitride is conformally deposited by chemical vapor deposition.

50. (Amended) The capacitor of claim 46, wherein the layer of [only] tungsten nitride is exposed to silicon based materials, and wherein a boundary between the layer of [only] tungsten nitride and the silicon based materials is characterized by a reduced encroachment of the tungsten nitride into the silicon based materials.

52. (Amended) A capacitor, comprising:

a first electrode formed as a layer of [only] tungsten nitride, the layer of tungsten nitride including silicon;

a dielectric disposed on the first electrode; and

a second electrode formed on the dielectric.

55. (Amended) The capacitor of claim 52, wherein the layer of [only] tungsten nitride is conformally deposited by chemical vapor deposition.

56. (Amended) The capacitor of claim 52, wherein the layer of [only] tungsten nitride is exposed to silicon based materials, and wherein a boundary between the layer of [only] tungsten nitride and the silicon based materials is characterized by a reduced encroachment of the tungsten nitride into the silicon based materials.

58. (Amended) A non-planar capacitor, comprising:  
a polycrystalline silicon film;  
a dielectric layer disposed on the polycrystalline film; and  
a film of [only] tungsten nitride disposed on the dielectric layer, the film of tungsten nitride including silicon.
61. (Amended) The non-planar capacitor of claim 58, wherein the film of [only] tungsten nitride is conformally deposited by chemical vapor deposition.
62. (Amended) A non-planar capacitor, comprising:  
a conformal polycrystalline silicon film formed over a substrate and over transistor devices on the substrate;  
a dielectric layer formed on the conformal polycrystalline silicon film; and  
a film of [only] tungsten nitride conformally deposited on the dielectric layer by chemical vapor deposition, the film of tungsten nitride including silicon.
63. (Amended) The non-planar capacitor of claim 62, wherein the film of [only] tungsten nitride is formed by a chemical vapor deposition process that uses ammonia as a source of nitrogen and a gas selected from the group consisting of tungsten hexafluoride and tungsten carbonyl as a source of tungsten.
64. (Amended) The non-planar capacitor of claim 62, wherein the film of [only] tungsten nitride is formed by a chemical vapor deposition process that uses a source gas mixture that includes:  
ammonia;  
a gas selected from the group consisting of tungsten hexafluoride and tungsten carbonyl;  
and  
a gas selected from the group consisting of silane, organic silane, and a compound that is a multiple order of silane.

66. (Amended) A non-planar capacitor, comprising:
- a first electrode;
  - a dielectric layer formed on the first electrode; and
  - a film of [only] tungsten nitride conformally deposited on the dielectric layer by chemical vapor deposition that uses gases, including:
    - ammonia;
    - a gas selected from the group consisting of tungsten hexafluoride and tungsten carbonyl; and
    - a gas selected from the group consisting of silane, organic silane, and a compound that is a multiple order of silane.
69. (Amended) An integrated circuit, comprising:
- a substrate;
  - at least one transistor device formed on the substrate and arranged to leave a contact area with the substrate;
  - a non-planar capacitor, including:
    - a first electrode;
    - a second electrode; and
    - a dielectric disposed between the first and the second electrode,wherein at least one of the first electrode and the second electrode includes [only]  
a tungsten nitride layer, and the tungsten nitride layer includes silicon.
70. (Amended) The integrated circuit of claim 69, wherein both the first electrode and the second electrode includes [only] a tungsten nitride layer, and the tungsten nitride layer includes silicon.
71. (Amended) The integrated circuit of claim 69, wherein the first electrode includes [only] a tungsten nitride layer, and the tungsten nitride layer includes silicon.